DFS400CL17I3C2

1700V/400A Chopper SiC MOSFET Module

Description

The DFS400CU17I3C2 is a Chopper SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as xEV Application and Renewable energy.

Features

- Blocking voltage 1700V
- $R_{DS(on)}$ =5.2mΩ (V_{GS} =15V)
- Low thermal resistance with Si_3N_4 AMB
- 175°C maximum junction temperature
- Low Inductive Design
- Thermistor inside
- Pressfit terminal
- Copper base size: 79mm*62mm

Applications

- xEV Applications
- Converter
- Vehicle Fast Chargers
- Renewable energy

Circuit diagram

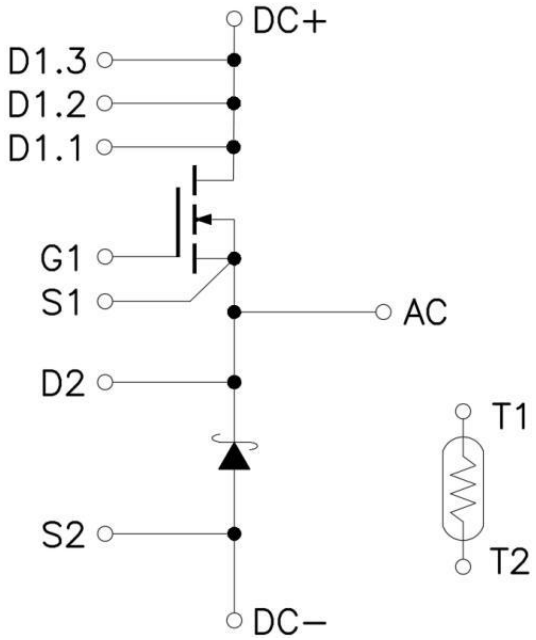


Figure 1. Out drawing & circuit diagram for DFS400CU17I3C2

Pin Configuration and Marking Information

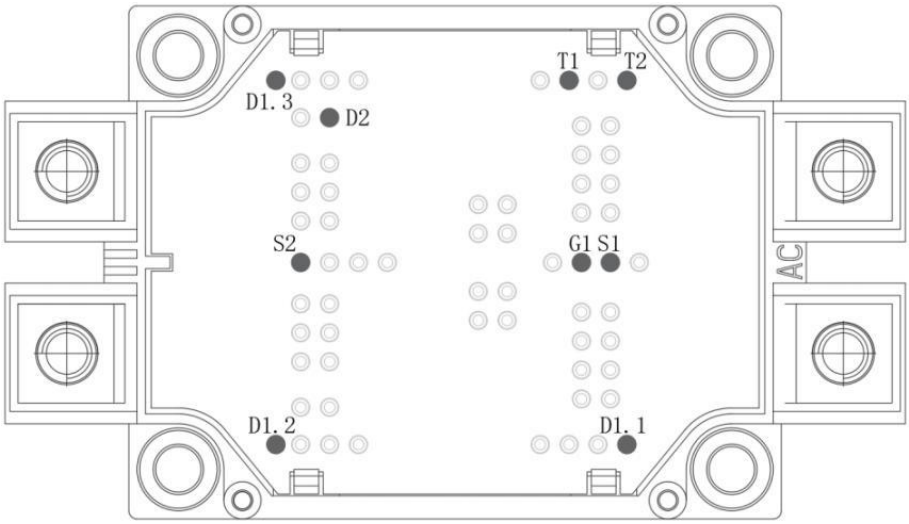


Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f=50Hz, t =1min	4	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 10	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	600	-
Module lead resistance, terminals-chip	T_C =25°C	0.5	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	250	g

Maximum Ratings (T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-Source Voltage	G-S Short	1700	V
V_{GSS}	Gate-Source Voltage (+)	D-S Short	20	V
V_{GSS}	Gate-Source Voltage (-)	D-S Short	-10	V
$V_{GSSSurge}$	G-S Voltage(t_{surge} <300nsec)	D-S Short, Note1	-10 to 20	V
I_{DS}	DC Continuous Drain Current	T_f=25°C, V_{GS} =15V	420	A
I_{DS}	DC Continuous Drain Current	T_f=65°C, V_{GS} =15V	360	A
I_{DSM}	Pulse Forward Current	T_f=25°C, Pulse width =1ms, V_{GS} =15V, Note2	800	A
I_F	Forward Current (Diode)	T_f=65°C	430	A
I_{FRM}	Pulse Forward Current (Diode)	Less than 1ms, Note2	800	A
I^2t	$\int I^2dt$	T_P =10ms, T_C =25℃	11248	A^2S
P_{tot}	Total Power Dissipation	T_C =25°C	2585	W
T_{jmax}	Max Junction Temperature	-	175	°C
T_{stg}	Storage Temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, -4V/+15V， -5V/+15V

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R_{25}	Resistance	T_C =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T_C =100°C, R_{100} =493Ω	5	-	5	%
P_{25}	Power dissipation	T_C =25°C	-	-	20	mW
$B_{25/50}$	B-value	R2 =R25 exp [$B_{25/50}$(1/T2 - 1/(298,15 K))]	-	3375	-	K
$B_{25/80}$	B-value	R2 =R25 exp [$B_{25/80}$(1/T2 - 1/(298,15 K))]	-	3411	-	K
$B_{25/100}$	B-value	R2 =R25 exp [$B_{25/100}$(1/T2 - 1/(298,15 K))]	-	3433	-	K

MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} =0V, I_D =160uA		1700	-	-	V
I_{DSS}	Zero gate voltage drain Current	V_{DS}=1700V, V_{GS}=0V		-	4	160	μA
$V_{GS(th)}$	Gate-source threshold Voltage	I_D=240mA V_{DS}=V_{GS}	T_j =25°C	1.8	2.7	-	V
			T_j=175°C	-	1.90	-	V
I_{GSS}	Gate-Source Leakage Current	V_{GS} =15V, V_{DS} =0V, T_j=25°C		-	-	1000	nA
$R_{DS(on)}$ (Chip)	Static drain-source On-state resistance	I_D=400A V_{GS}=15V	T_j=25°C	-	5.2	7.5	mΩ
			T_j=175°C	-	11.6	-	mΩ
$V_{DS(on)}$ (Chip)	Static drain-source On-state Voltage	I_D=400A V_{GS}=15V	T_j=25°C	-	2.08	3.0	V
			T_j=175°C	-	4.64	-	V
V_{SD}	Body Diode Forward Voltage	V_{GS} =0V I_{SD} =400A	T_j=25°C	-	4.8	-	V
			T_j=175°C	-	4.2	-	V
C_{iss}	Input Capacitance	V_D=1000V, V_{GS}=0V f=1MHz, Vac=25mV		-	30.5	-	nF
C_{oss}	Output Capacitance			-	0.82	-	nF
C_{rss}	Reverse transfer Capacitance			-	0.15	-	nF
Q_G	Total gate charge	V_{DD}=1000V, I_D=300A, V_{GS}=-5/+15V		-	1022	-	nC
R_{Gint}	Internal Gate Resistance	T_j =25°C		-	0.48	-	Ω
$t_{d(on)}$	Turn-on delay time	V_{DD}=900V I_D=400A V_{GS}=+15/-4V $R_{G(on)}$=6.8Ω $R_{G(off)}$=6.8Ω Inductive load switching operation	T_j=25°C	-	165	-	ns
			T_j=150°C	-	129	-	
t_r	Rise time		T_j=25°C	-	123	-	ns
			T_j=150°C	-	93	-	
$t_{d(off)}$	Turn-off delay time		T_j=25°C	-	515	-	ns
			T_j=150°C	-	646	-	
t_f	Fall time		T_j=25°C	-	80	-	ns
			T_j=150°C	-	102	-	
E_{on}	Turn-on power dissipation		T_j=25°C	-	48.4	-	mJ

			T_j =150°C	-	40.7	-	
E_{off}	Turn-off power dissipation		T_j =25°C	-	46.1	-	mJ
			T_j =150°C	-	49.6	-	
$R_{th(j-c)}$	FET Thermal Resistance	Junction to Case		-	0.058	-	K/W
$R_{th(c-f)}$	Contact thermal Resistance	With thermal conductive grease, Note1		-	0.015	-	K/W

Note1: Assumes Thermal Conductivity of grease is 0.9W/m·K and thickness is 50um.

SiC SBD Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_{RRM}	Repetitive Peak Reverse Voltage	T_j =25°C		-	1700	-	V
V_F	Forward Voltage	I_F =400A	T_j =25°C	-	1.8	-	V
			T_j =175°C	-	2.9	-	
I_{RRM}	Reverse Current	V_{RRM} =1700V	T_j =25°C	-	8	200	uA
			T_j =175°C	-	164	-	
Q_C	Total Capacitive Charge	$I_F \leqslant I_{F,MAX}$ dI$_F$/dt =200A/μS	V_R=600V	-	1432	-	nc
			V_R=1200V	-	2096	-	
C	Total Capacitance	f=1MHz	V_R =1V	-	18308	-	pF
			V_R=1200V	-	1008	-	
T_{rr}	Reverse recovery time	V_{RR} =600V, I_F =400A V_{GS} =+15/-4V R_G =6.8Ω Inductive load	T_j =25°C	-	19	-	ns
			T_j =150°C	-	17	-	
E_{rr}	Diode switching power dissipation		T_j =25°C	-	0.81	-	mJ
			T_j =150°C	-	1.08	-	
$R_{th(j-c)}$	SiC SBD Thermal Resistance	Junction to Case		-	0.063	-	K/W
$R_{th(c-f)}$	Contact thermal Resistance	With thermal conductive grease, Note1		-	0.015	-	K/W

Note1: Assumes Thermal Conductivity of grease is 2.8W/m·K and thickness is 50um.

Test Conditions

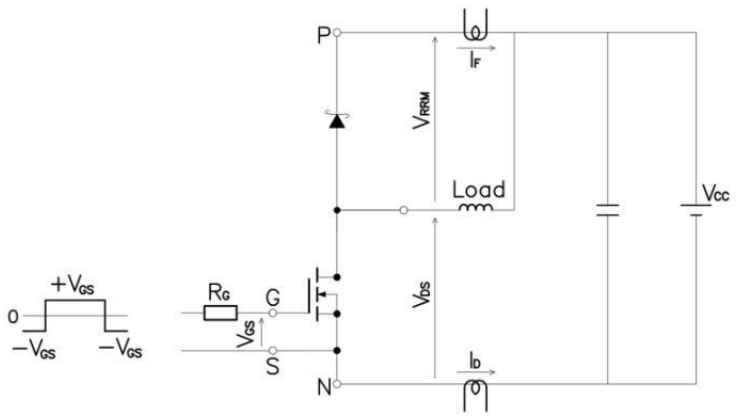


Figure 3. Switching time measure circuit

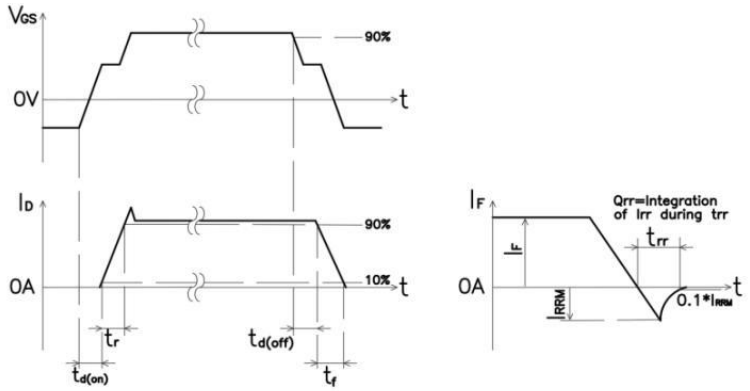


Figure 4. Switching time definition

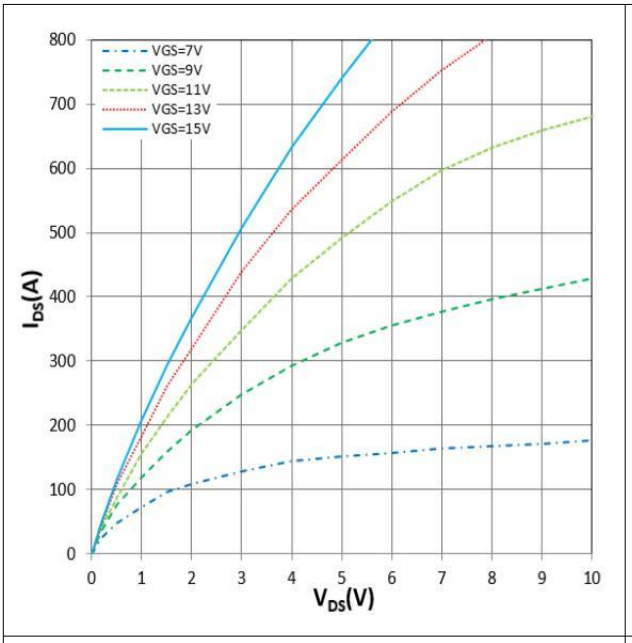


Figure 5. I_{DS} vs V_{DS}

T_j=25°C, V_{GS} parameter

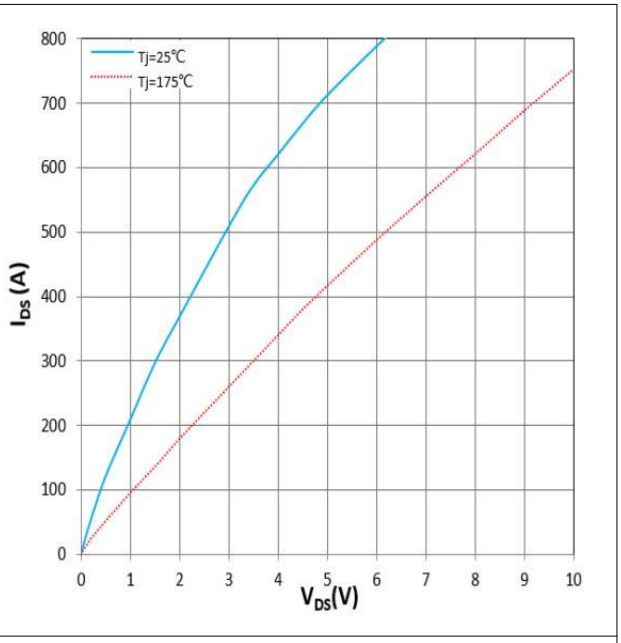


Figure 6. I_{DS} vs V_{DS}

V_{GS}=15V, T_j parameter

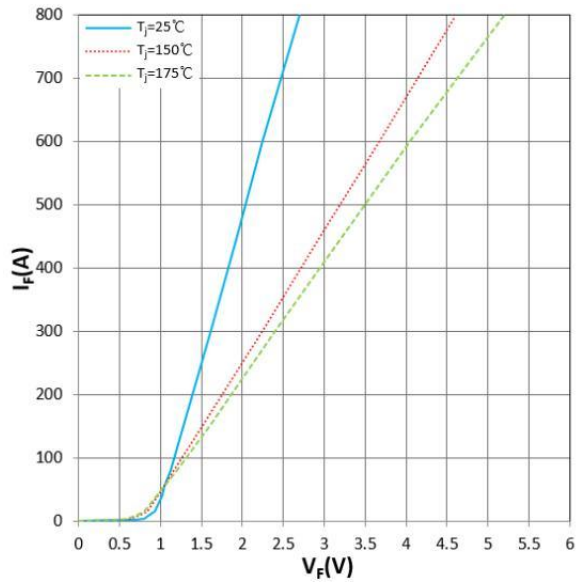


Figure 7. I_F vs V_F

T_j parameter

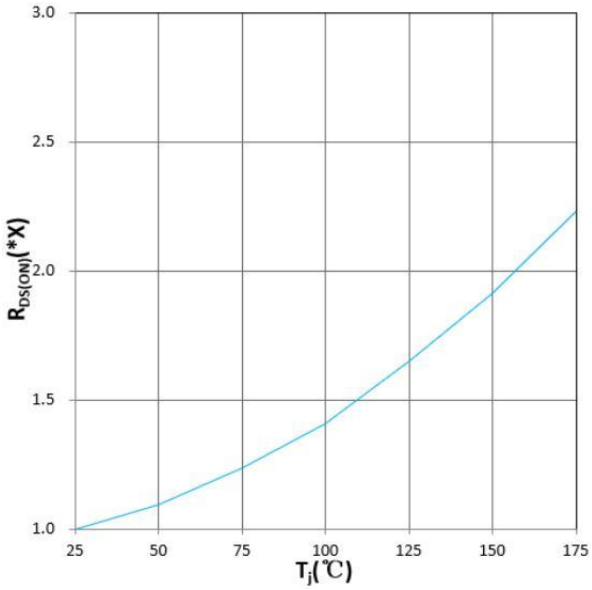


Figure 8. $R_{DS(ON)}$ vs T_j

V_{GS}=+15V, I_D=400A, 1.0X=5.2mΩ

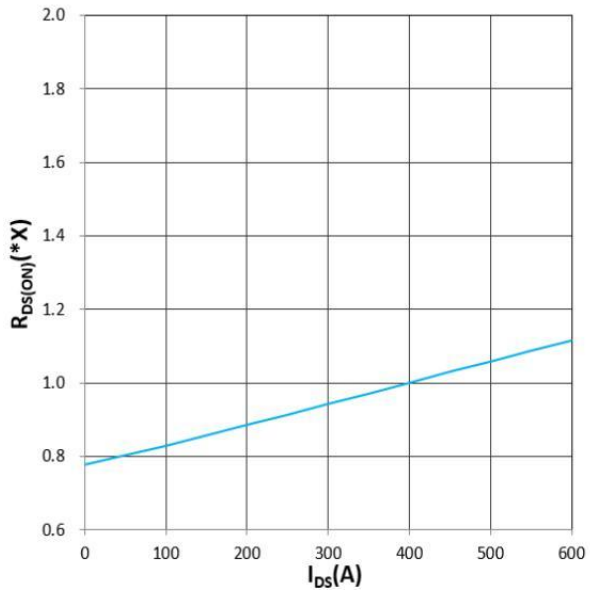


Figure 9. $R_{DS(ON)}$ vs I_{DS}

T_j =25℃,V_{GS}=+15V, 1.0X=5.2mΩ

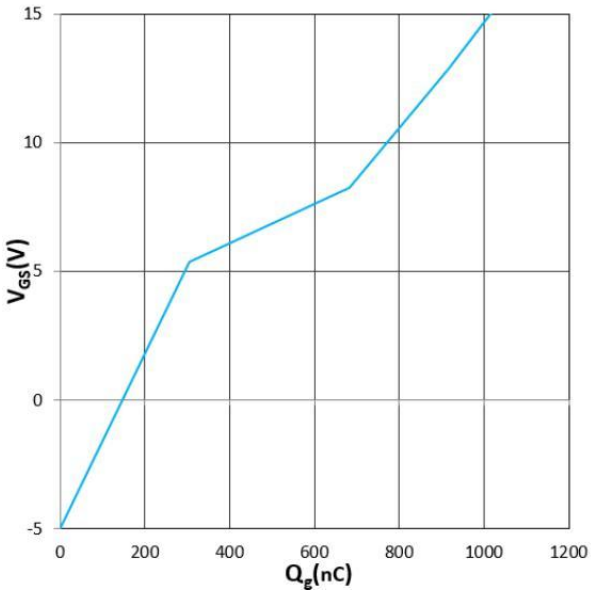


Figure 10. V_{GS} vs Q_g

T_j =25℃, V_{DS} =1000V, I_D=300A

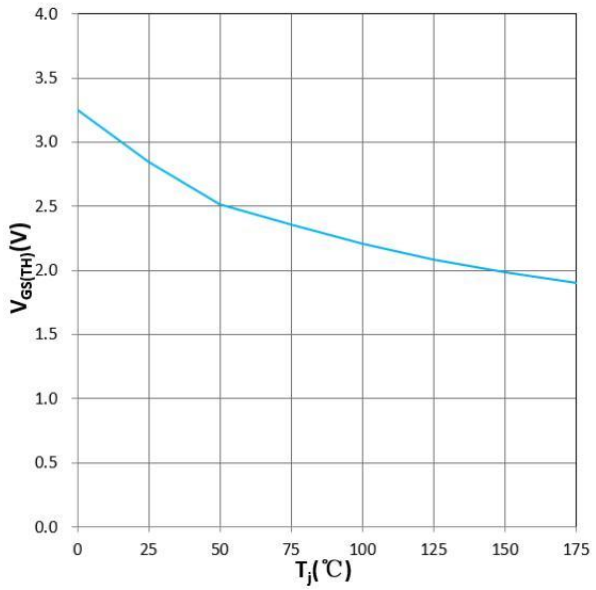


Figure 11. $V_{GS(TH)}$ vs T_j

V_{GS} =V_{DS} , I_D =240mA

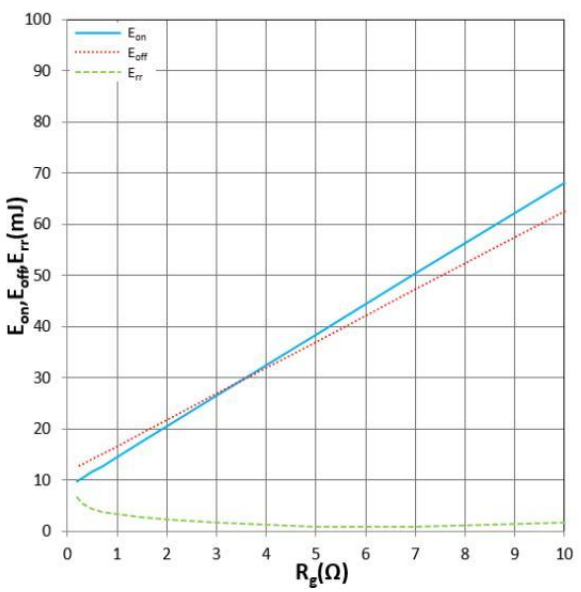


Figure 12. E_{on}, E_{off}, E_{rr} vs R_g

T_j =25°C, V_{CC} =900V, V_{GS} =+15V/-4V, I_D =400A

Inductive Load

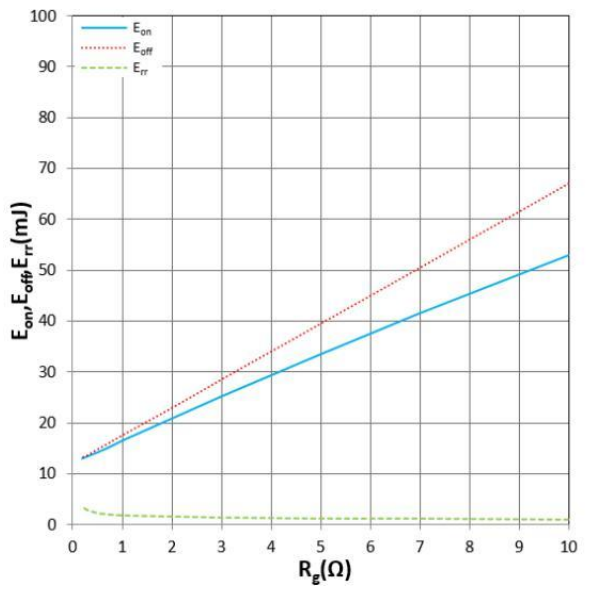


Figure 13. E_{on}, E_{off} , E_{rr} vs R_g

T_j =150°C, V_{CC} =900V, V_{GS} =+15V/-4V, I_D =400A

Inductive Load

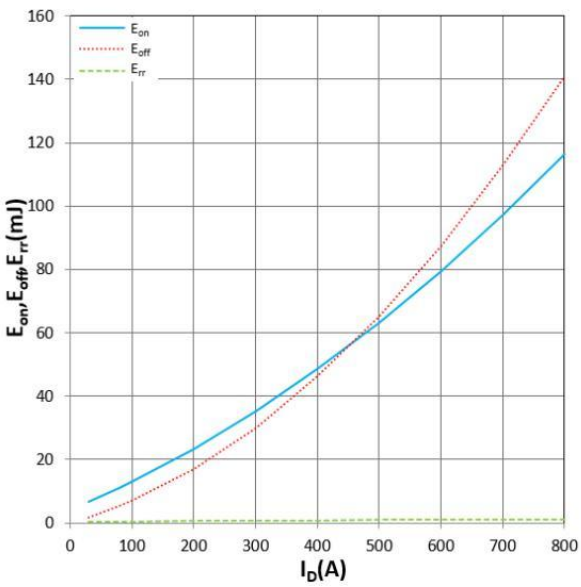


Figure 14. E_{on}, E_{off}, E_{rr} vs I_D

T_j =25°C, V_{CC} =900V, V_{GS} =+15V/-4V, R_g =6.8Ω

Inductive Load

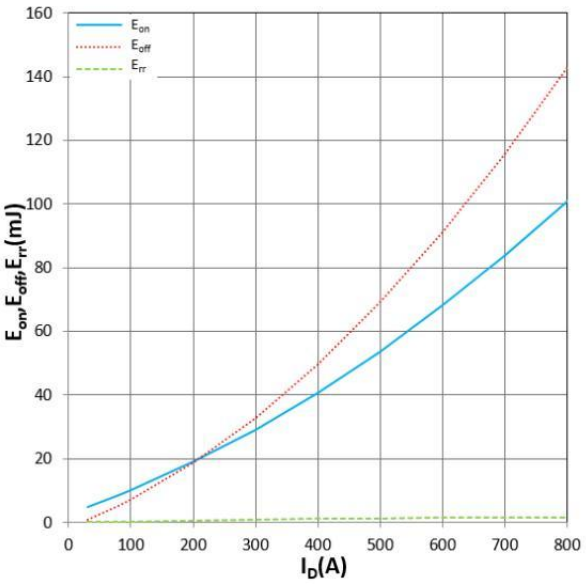
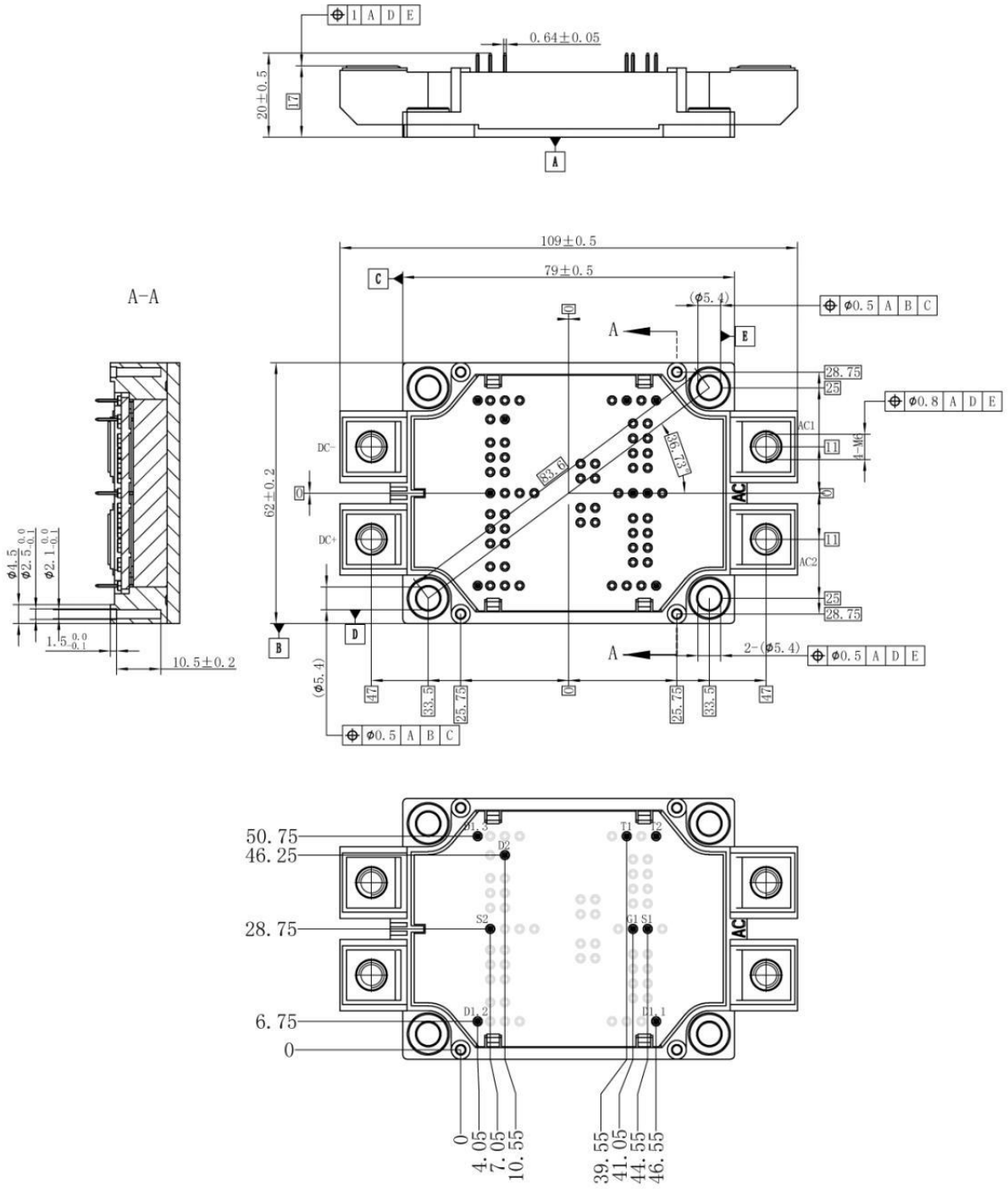


Figure 15. E_{on}, E_{off}, E_{rr} vs I_D

T_j=150°C, V_{CC}=900V, V_{GS}=+15V/-4V, R_g=6.8Ω

Inductive Load

Package dimensions



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